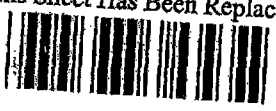
This Sheet Has Been Replaced



ABSTRACT OF THE DISCLOSURE

With a method according to the invention, a semiconductor article such as an SOI substrate having on the surface thereof a single crystal silicon film formed on an insulator is etched by heat treatment in a hydrogen-containing reducing atmosphere in order to remove the surface by a desired height and smooth it. The method is characterized in that the single crystal silicon film is arranged opposite to silicon oxide in a furnace during the etching process.